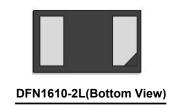


Transient Voltage Suppressor

Description

The PTVSHC2EN15V3 Transient Voltage Suppressor is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. The PTVSHC2EN15V3 protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events.



Feature

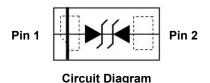
- \triangleright 2000W peak pulse power per line (t_P = 8/20µs)
- DFN1610-2L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping Voltage
- Transient protection for data lines to IEC 61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

15N3

Marking (Top View)

Applications

- > Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals

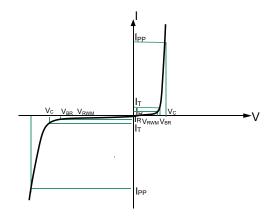


Mechanical Characteristics

- Lead finish:100% matte Sn(Tin)
- ➤ Qualified max reflow temperature:260°C
- ➤ Pure tin plating: 7 ~ 17 um
- ➤ Pin flatness: ≤3mil
- Device meets MSL 3 requirements
- RoHS compliant

Electronics Parameter

Symbol	Parameter	
V _{RWM}	Peak Reverse Working Voltage	
I _R	Reverse Leakage Current @ V _{RWM}	
V _{BR}	Breakdown Voltage @ I⊤	
lτ	Test Current	
I _{PP}	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ I _{PP}	
P _{PP}	Peak Pulse Power	



Electrical characteristics per line@25℃(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Reverse Working Voltage	V _{RWM}	Pin1 to Pin2	-	-	15.0	V
Reverse Breakdown Voltage	V _{BR}	Pin1 to Pin2, I _T =1mA	16.5	-	20.5	V
Reverse Current	I _R	Pin1 to Pin2, V _{RWM} =15V	-	-	1.0	μA
Clamping Voltage	Vc	Pin1 to Pin2, I _{PP} =30A,T _P =8/20µs	22	24	26	V
Clamping Voltage	Vc	Pin1 to Pin2, I _{PP} =75A, T _P =8/20µs	28	31	34	V
Reverse Working Voltage	V _{RWM}	Pin2 to Pin1	-	-	3.3	V
Reverse Breakdown Voltage	V_{BR}	Pin2 to Pin1, I _T =1mA	3.4	-	5	٧
Reverse Current	I _R	Pin2 to Pin1, V _{RWM} =3.3V	-	-	5.0	μA
Clamping Voltage	Vc	Pin2 to Pin1, I _{PP} =30A,T _P =8/20µs	5	7	9	V
Clamping Voltage	Vc	Pin2 to Pin1, I _{PP} =75A,T _P =8/20µs	9	11	13	V
Junction Capacitance	CJ	V _R =0V f = 1MHz	-	90	-	pF

Absolute maximum rating@25℃

Rating	Symbol	Value	Unit
Peak Pulse Power (t _P = 8/20µS,Pin1 to Pin2)	P _{pp}	2000	W
Peak Pulse Power (t _P = 8/20µS,Pin2 to Pin1)	P _{PP}	650	W
Peak Pulse Current (t _p =8/20μS)	I _{PP}	75	А
Operating Temperature	Tu	-55 to +150	$^{\circ}$ C
Storage Temperature	T _{STG}	-55 to +150	°C

Typical Characteristics

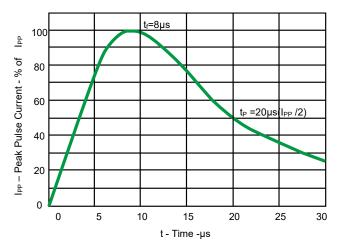
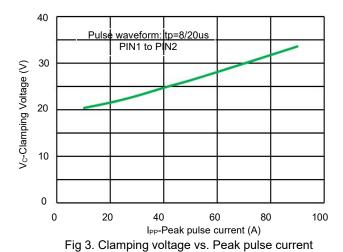


Fig 1. Pulse Waveform



100 80 60 20 0 25 50 75 100 125 150 T_L – Lead Temperature - °C

Fig 2. Power Derating Curve

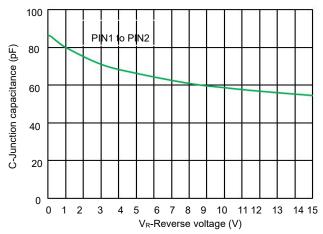
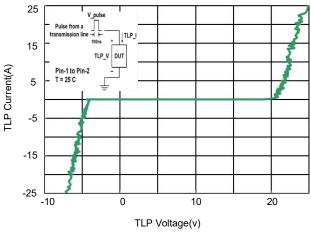


Fig 4. Capacitance vs. Reveres voltage



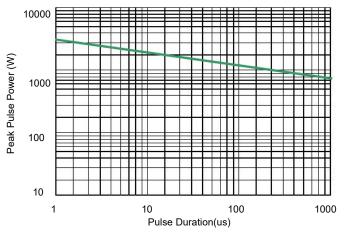
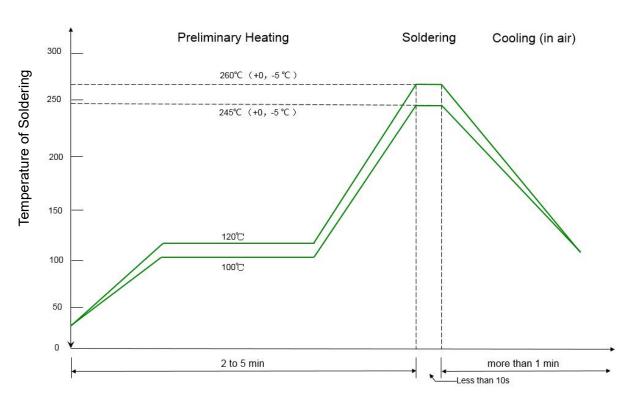


Fig 5. TLP Measurement

Fig 6. Non-Repetitive Peak Pulse Power vs Pulse time

Solder Reflow Recommendation



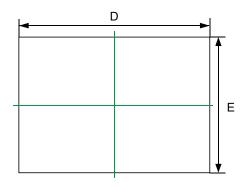
Remark: Pb free for 260°C; Pb for 245°C.

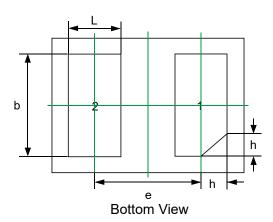
PCB Design

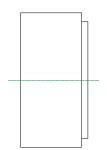
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

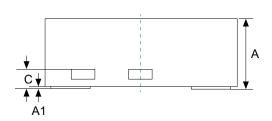
- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- > Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

Product dimension (DFN1610-2L)

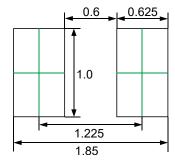








Dim	Millimeters		
	MIN	MAX	
А	0.45	0.60	
A1		0.05	
b	0.75	0.85	
С	0.10	0.20	
D	1.55	1.65	
е	1.10BSC		
E	0.95 1.05		
L	0.35	0.45	
h	0.15	0.25	



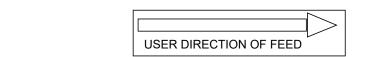
Recommended Soldering Pad

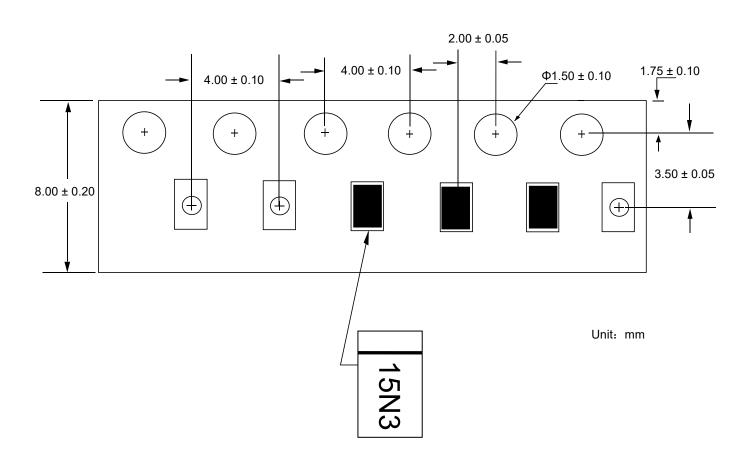
Unit: mm

Ordering information

Device	Package	MPQ
PTVSHC2EN15V3	DFN1610-2L (Pb-Free)	3000 / Tape & Reel

Load with information





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